

Notice of References Cited

Application/Control No.

10/567,729

Applicant(s)/Patent Under
Reexamination
KOJIMA ET AL.

Examiner

SARAH K. SALERNO

Art Unit

2814

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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2006/0011128	01-2006	Ellison et al.	117/084
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Nakamura et al., "Surface Mechanisms in Homoepitaxial Growth on alpha-SiC {0001}-vicinal Faces;" Silicon Carbide and Related Materials; Material Science Forum; 2003; pages 163-168.
	V	Kojima et al., "4H-SiC Carbon-Face Epitaxial Layers Grown by Low Pressure Hot-Wall Chemical Vapor Deposition;" Material Science Forum; 2003; pages 209-212; Volumes 457-460; Trans Tech Publications; Switerland.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.